NPN switching transistor PZT2222A

FEATURES

- High current (max. 600 mA)
- Low voltage (max. 40 V).

APPLICATIONS

- Switching and linear amplification.

DESCRIPTION

NPN switching transistor in a SOT223 plastic package.
PNP complement: PZT2907A.

PINNING

PIN	DESCRIPTION
1	base
2, 4	collector
3	emitter

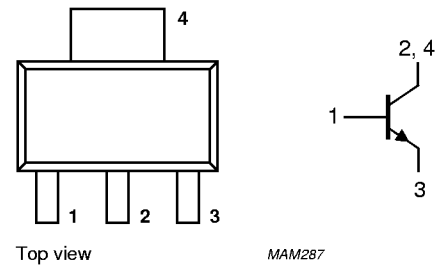


Fig.1 Simplified outline (SOT223) and symbol.

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CBO}	collector-base voltage	open emitter	–	75	V
V_{CEO}	collector-emitter voltage	open base	–	40	V
V_{EBO}	emitter-base voltage	open collector	–	6	V
I_C	collector current (DC)		–	600	mA
I_{CM}	peak collector current		–	800	mA
I_{BM}	peak base current		–	200	mA
P_{tot}	total power dissipation	$T_{amb} \leq 25$ °C; note 1	–	1.15	W
T_{stg}	storage temperature		−65	+150	°C
T_j	junction temperature		–	150	°C
T_{amb}	operating ambient temperature		−65	+150	°C

Note

1. Device mounted on a printed-circuit board, single-sided copper, tinplated, mounting pad for collector 1 cm^2. For other mounting conditions, see *"Thermal considerations for SOT223 in the General Part of associated Handbook"*.

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j\text{-}a}$	thermal resistance from junction to ambient	note 1	109	K/W
$R_{th\ j\text{-}s}$	thermal resistance from junction to soldering point		28	K/W

Note

1. Device mounted on a printed-circuit board, single-sided copper, tinplated, mounting pad for collector 1 cm^2. For other mounting conditions, see *"Thermal considerations for SOT223 in the General Part of associated Handbook"*.

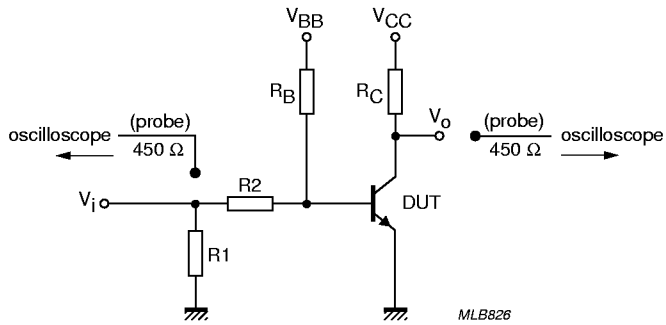
CHARACTERISTICS

T_j = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
I_{CBO}	collector cut-off current	I_E = 0; V_{CB} = 60 V	–	10	nA
		I_E = 0; V_{CB} = 60 V; T_{amb} = 125 °C	–	10	μA
I_{EBO}	emitter cut-off current	I_C = 0; V_{EB} = 5 V	–	10	nA
h_{FE}	DC current gain	I_C = 0.1 mA; V_{CE} = 10 V	35	–	
		I_C = 1 mA; V_{CE} = 10 V	50	–	
		I_C = 10 mA; V_{CE} = 10 V	75	–	
		I_C = 10 mA; V_{CE} = 10 V; T_{amb} = −55 °C	35	–	
		I_C = 150 mA; V_{CE} = 1 V; note 1	50	–	
		I_C = 150 mA; V_{CE} = 10 V; note 1	100	300	
		I_C = 500 mA; V_{CE} = 10 V; note 1	40	–	
V_{CEsat}	collector-emitter saturation voltage	I_C = 150 mA; I_B = 15 mA	–	300	mV
		I_C = 500 mA; I_B = 50 mA	–	1	V
V_{BEsat}	base-emitter saturation voltage	I_C = 150 mA; I_B = 15 mA	0.6	1.2	V
		I_C = 500 mA; I_B = 50 mA	–	2	V
C_c	collector capacitance	$I_E = i_e$ = 0; V_{CB} = 10 V; f = 1 MHz	–	8	pF
C_e	emitter capacitance	$I_C = i_c$ = 0; V_{EB} = 500 mV; f = 1 MHz	–	25	pF
f_T	transition frequency	I_C = 20 mA; V_{CE} = 20 V; f = 100 MHz	300	–	MHz
Switching times (between 10% and 90% levels); (see Fig.2)					
t_{on}	turn-on time	I_{Con} = 150 mA; I_{Bon} = 15 mA; I_{Boff} = −15 mA; T_{amb} = 25 °C	–	35	ns
t_d	delay time		–	10	ns
t_r	rise time		–	25	ns
t_{off}	turn-off time		–	250	ns
t_s	storage time		–	200	ns
t_f	fall time		–	60	ns

Note

1. Pulse test: $t_p \leq 300\ \mu s$; $\delta \leq 0.02$.

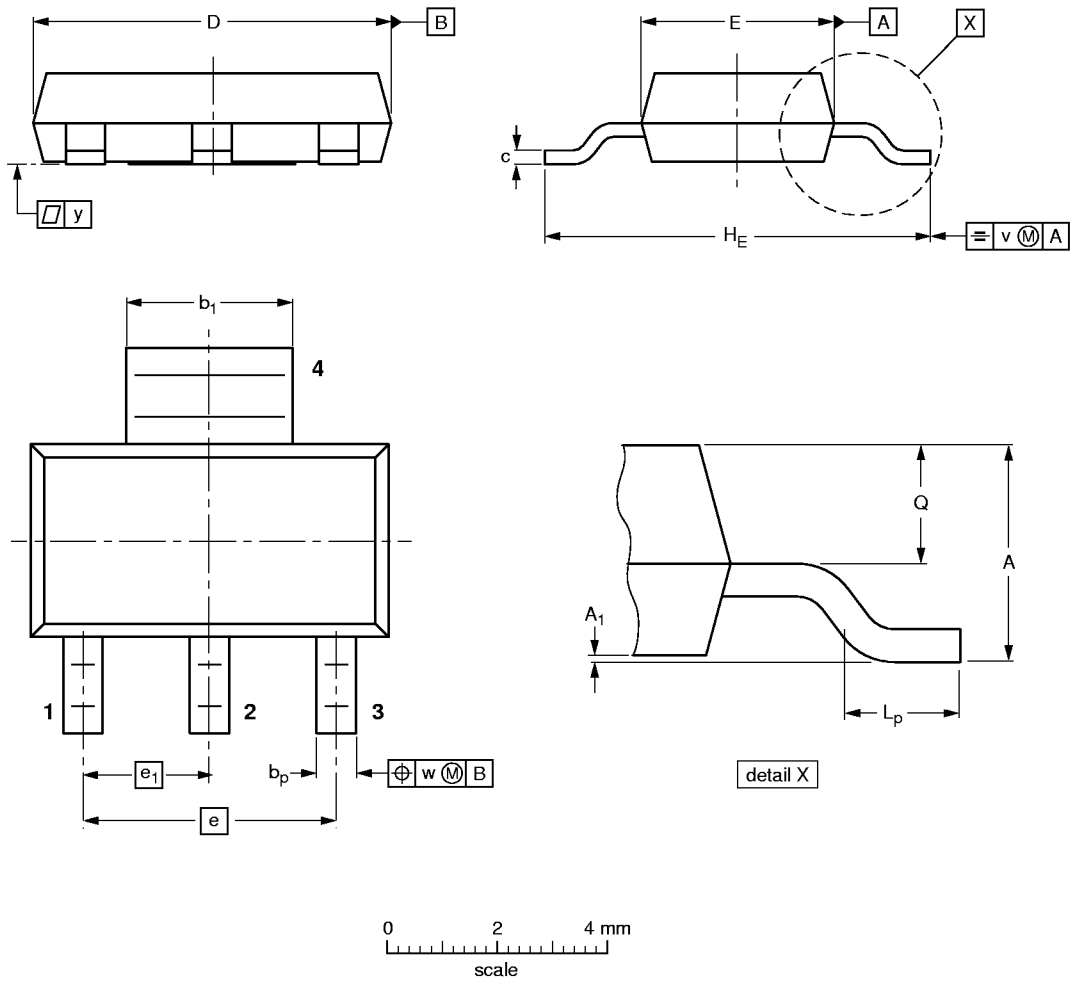


V_i = 9.5 V; T = 500 µs; t_p = 10 µs; $t_r = t_f \leq 3$ ns.
R1 = 68 Ω; R2 = 325 Ω; R_B = 325 Ω; R_C = 160 Ω.
V_{BB} = −3.5 V; V_{CC} = 29.5 V.
Oscilloscope input impedance Z_i = 50 Ω.

Fig.2 Test circuit for switching times.

PACKAGE OUTLINE

Plastic surface mounted package; collector pad for good heat transfer; 4 leads **SOT223**



DIMENSIONS (mm are the original dimensions)

UNIT	A	A_1	b_p	b_1	c	D	E	e	e_1	H_E	L_p	Q	v	w	y
mm	1.8 1.5	0.10 0.01	0.80 0.60	3.1 2.9	0.32 0.22	6.7 6.3	3.7 3.3	4.6	2.3	7.3 6.7	1.1 0.7	0.95 0.85	0.2	0.1	0.1

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT223						~~96-11-11~~ 97-02-28